Monolithic Amplifier

DC-7 GHz

Product Features

- High Gain, 20 dB typ. at 100 MHz
- High Pout, P1dB 18 dBm typ.
- High IP3, 33 dBm typ. at 100 MHz
- Ruggedized Design
- 5V operation
- Unconditionally stable
- Excellent ESD Protection
- Transient protected, US patent 6,943,629



GVA-83+

CASE STYLE: DF782 PRICE: \$1.82 ea. QTY. (25)

+ RoHS compliant in accordance with EU Directive (2002/95/EC)

The +Suffix has been added in order to identify RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications.

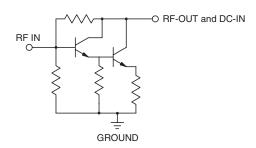
Typical Applications

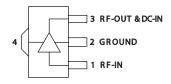
- · Base station infrastructure
- Portable Wireless
- CATV & DBS
- MMDS & Wireless LAN
- LTE

General Description

GVA-83+ (RoHS compliant) is a wideband amplifier offering high dynamic range. Lead finish is SnAgNi. It has repeatable performance from lot to lot and is enclosed in a SOT-89 package. It uses patented Transient Protected Darlington configuration and is fabricated using InGaP HBT technology.

simplified schematic and pin description





Function	Pin Number	Description
RF IN	1	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
RF-OUT and DC-IN	3	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection. Rbias in series with RF choke is required to obtain proper device voltage, as shown in "Recommended Application Circuit", Fig. 2
GND	2,4	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.





Electrical Specifications⁽¹⁾ at 25°C. 5V. Rb=7.5Ω. unless noted

Parameter	Condition (GHz)	Min.	Тур.	Max.	Units
requency Range ⁽²⁾	. ,	DC		7	GHz
Gain	0.1	18.4	20.5	22.6	dB
	1.0		19.3		
	2.0	15.4	17.1	18.8	
	3.0		15.2		
	4.0	12.0	13.8	15.2	
	6.0		12.3		
	7.0		11.2		
Magnitude of Gain Variation versus Temperature(3)	0.1		0.008		dB/°C
values are negative)	1.0		0.0034		
	2.0		0.0045	0.0090	
	3.0		0.0061		
	4.0 6.0		0.0009 0.0123		
	7.0				
			0.0120		-ID
nput Return Loss	0.1		41.0		dB
	1.0 2.0	13.0	26.0 19.5		
	3.0	13.0	17.7		
	4.0		17.7		
	6.0		19.1		
	7.0		14.1		
Output Return Loss	0.1		14.2		dB
output Hetarri Loss	1.0		13.1		
	2.0	8.0	11.2		
	3.0		10.2		
	4.0		10.8		
	6.0		11.6		
	7.0		9.7		
leverse Isolation	2.0		26.5		dB
Output Power @1 dB compression	0.1	16.5	18.1		dBm
	1.0	16.5	18.5		
	2.0	16.5	18.6		
	3.0		18.4		
	4.0		18.1		
	6.0		18.1		
	7.0		17.3		ID.
Output IP3	0.1		33.0		dBm
	1.0 2.0	29.0	32.5 31.5		
	3.0	29.0	31.3		
	4.0		31.2		
	6.0		29.3		
	7.0		28.5		
Isiaa Figura	0.1		5.9	7.0	dB
Noise Figure	1.0		6.0	7.0	ub.
	2.0		6.2	7.3	
	3.0		6.2		
	4.0		6.5		
	6.0		7.2		
	7.0		7.5		
iroup Delay			100		psec
evice Operating Voltage		4.8	5.0	5.2	· v
			+		
evice Operating Current		61	72	82	mA
evice Current Variation vs. Temperature			28		μΑ/°C
·					1
revice Current Variation vs. Ferriporadire			0.030		mA/mV





⁽¹⁾ Measured on Mini-Circuits test board TB-313. See Characterization Test Circuit (Fig. 1)
(2) Guaranteed specification DC*-7 GHz. *Low frequency cut off determined by external coupling capacitors and RF Choke (RFC)
(3) (Gain at 85°C-Gain at -45°C)/130

Absolute Maximum Ratings

Parameter	Ratings		
Operating Temperature (ground lead)	-40°C to 85°C		
Storage Temperature	-65°C to 150°C		
Operating Current at 5V w/7.5ΩRbias	120mA		
Power Dissipation	0.74W		
Input Power	20dBm		
DC Voltage on Pin 3	5.8V		

Permanent damage may occur if any of these limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.

Characterization Test Circuit

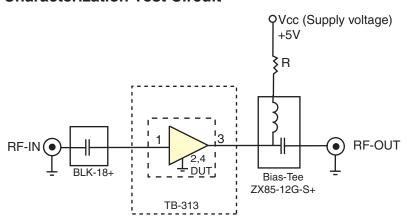


Fig 1. Block Diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Test Board TB-313)

Gain, Output power at 1dB compression (P1 dB) and output IP3 (OIP3) are measured using R&S Network Analyzer ZVA-24. Noise Figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

- 1. Total resistance (Rb) of DC bias path equal 7.5Ω
- 2. Gain and Return Loss: Pin= -25dBm
- 3. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0 dBm/tone at output.





Product Marking



Additional Detailed Technical Information

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter data set (S2P FILES) (.zip file)

Case Style: DF782 (SOT 89)

Plastic package, exposed paddle, lead finish: tin/silver/nickel

Tape & Reel: F55

Suggested Layout for PCB Design: PL-255

Evaluation Board: TB-410-83+

Environmental Ratings: ENV08T1

Recommended Application Circuit

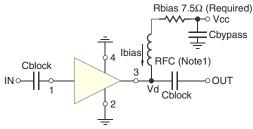


Fig 2. Test Board includes case, connectors, and components soldered to PCB.

Note 1. If DC resistance of RF Choke is > 0.5 Ω , reduce 7.5 Ω R_{bias} accordingly.





ESD Rating

Human Body Model (HBM): Class 1C (1000v to < 2000v) in accordance with ANSI/ESD STM 5.1 - 2001

Machine Model (MM): Class M2 (100V to < 200V) in accordance with ANSI/ESD STM 5.2 - 1999

MSL Rating

Moisture Sensitivity: MSL1 in accordance with IPC/JEDECJ-STD-020D

MSL Test Flow Chart

